

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L7	8378	257/239,261,295,298,314-326.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/12/01 14:50
L8	4675	L7 and (float\$3 near (gate electrode\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/12/01 14:50
L9	1581	L8 and (((element\$1 device\$1 circuit\$1) near isolat\$3) LOCOS STI)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/12/01 16:43
L10	1567	L9 and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/12/01 14:50
L11	1565	L10 and (ONO insulat\$3 oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/12/01 16:45
L12	74	L11 and concave	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/12/01 14:50
L13	6	("5994733" "6281050" "6342715" "6403421" "6417051" "6441426").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/01 15:52
L14	7	("5051795" "5661056" "5686333" "6184085" "6232632" "6246089" "6362045").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/01 16:02
L15	7	("4495693" "5466624" "5468677" "5498556" "5556798" "5556799" "5604141").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/01 16:42
L16	0	(((non near volatile) nonvolatile) near memory) AND (((element\$1 device\$1 circuit\$1) near isolat\$3) LOCOS STI) AND ((float\$3 near (gate electrode\$1)) FG) AND (ONO ((insulat\$3 oxide) near (layer film))) AND ((control near (gate electrode)) CG) AND (plural\$3 near step\$1) AND (tapered near concave) AND (extend\$3 with depth) AND interval.CLM.	US-PGPUB; USPAT	OR	ON	2005/12/01 16:55

L17	0	((non near volatile) nonvolatile) near memory) AND (((element\$1 device\$1 circuit\$1) near isolat\$3) LOCOS STI) AND ((float\$3 near (gate electrode\$1)) FG) AND (ONO ((insulat\$3 oxide) near (layer film))) AND ((control near (gate electrode)) CG) AND (plural\$3 near step\$1) AND concave AND (extend\$3 with depth) AND interval. CLM.	US-PGPUB; USPAT	OR	ON	2005/12/01 16:51
L18	0	((non near volatile) nonvolatile) near memory) AND (((element\$1 device\$1 circuit\$1) near isolat\$3) LOCOS STI) AND ((float\$3 near (gate electrode\$1)) FG) AND (ONO ((insulat\$3 oxide) near (layer film))) AND ((control near (gate electrode)) CG) AND plural\$3 AND step\$1 AND concave AND (extend\$3 with depth) AND interval. CLM.	US-PGPUB; USPAT	OR	ON	2005/12/01 16:51
L19	5	((non near volatile) nonvolatile) near memory) AND (((element\$1 device\$1 circuit\$1) near isolat\$3) LOCOS STI) AND ((float\$3 near (gate electrode\$1)) FG) AND (ONO ((insulat\$3 oxide) near (layer film))) AND ((control near (gate electrode)) CG) AND plural\$3 AND step\$1 AND concave AND interval.CLM.	US-PGPUB; USPAT	OR	ON	2005/12/01 16:52
L20	0	((non near volatile) nonvolatile) near memory) AND ((tapered (v near shape\$1)) near concave)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/12/01 16:56